

20A 200V SchottkyBarrierDiode

1 Description

Dual center tab Schottky rectifier suited for High Frequency server and telecom base station SMPS. Packaged in TO Inside the package, this device combineshigh current rating and low volume to enhance both reliability and power density of the application.

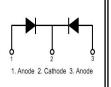
TO-220F provides insulation voltage rated at 2000V RMS from all three terminals to external heatsink.

2 Features

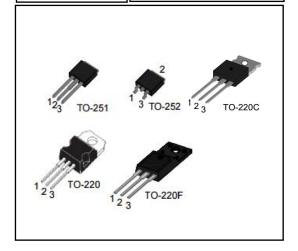
- High junction temperature capabiliy
- Low leakage current
- Low thermal resistance
- High frequency operation

3 Applications

- converters
- free-wheeling diodes
- reverse battery protection
- Typical applications are in switching power



 $V_{BR} = 200V$ $V_{F(single)(Max)} = 0.95V$ $I_{F(AV) (single)} = 10A$



4 Electrical Characteristics

4.1 Absolute Maximum Ratings (Tc=25 °C,unless otherwise noted)

PARAMETER			SYMBOL	VALUE	UNIT
Peak Repetitive Reverse Voltage			V _{RRM}	200	V
RMS Reverse Voltage			V _{R(RMS)}	160	V
DC Blocking Voltage			V _R	200	V
Average Rectified Forward Current(single)				10	Α
Average Rectified Forward Current(double)			I _{F(AV)}	20	Α
Repetitive Peak Surge Current(single)			I _{FRM}	15	Α
Nonrepetitive Peak Surge Current(single) tp=8.3ms		I _{FSM}	150	Α	
Reverse Surge Current (Note 1)			I _{RSM}	4	Α
Operating Junction Temperature Range			Tj	- 55∼150	$^{\circ}$ C
Storage Temperature Range			T _{stg}	-55~150	$^{\circ}$
ESD (Machine Model=C)				>400	V
ESD (Human Body Model=3B)				>8000	V
ESD(Noncontact)				>15000	V

4.2 Thermal Characteristics

PARAMETER	SYMBOL	VALUE			UNIT
PARAWETER		TO-220	TO-220F	TO-252/251	CINII
Thermal Resistance, Junction to Case-sink	R _{thJC}	2.8	4.8	4.5	°C/W



4.3 Electrical Characteristics

(Tc=25[°]C,unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Maximum Instantaneous	V_{F}	I _F =10A	-	0.87	0.95	V
Forward Voltage(Note 3)		I _F = 10A, T _C = 125℃	-	-	0.85	V
		I _F = 20A	-	0.95	1.20	V
Maximum Instantaneous	I _R	V _R = 200V	-	2	100	uA
Reverse (Note 2)		V _R = 200V, T _C = 125 °C	-	-	15	mA
Total capacitance	C _{tot}	V _R =4V f=1MHz	-	90	-	pF
DC Blocking Voltage	V_{BR}	I _R =100uA	205	230	-	V

Notes

- 1. 2.0us Pulse Width, f=1.0 KHz
- 2. Pulse Test: 300us Pulse Width, 1% Duty Cycle
- 3. VF Instantaneous forward voltage (pw = $300\mu s$, D = 2%).

5 Typical characteristics diagrams

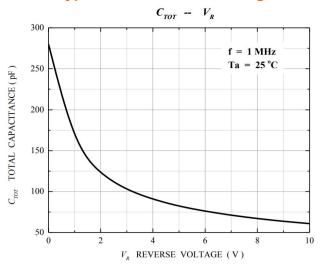


FIGURE 1. Total capacitance vs Voltage

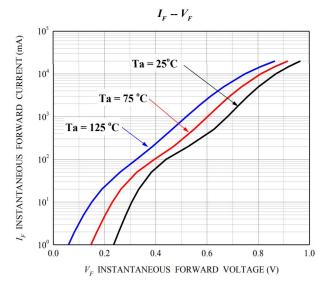


FIGURE 3. FORWARD CURRENT vs FORWARD VOLTAGE

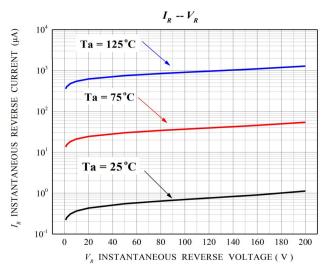


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

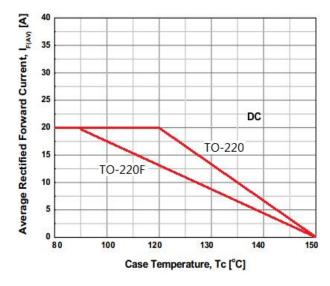


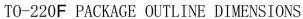
FIGURE 4. CURRENT DERATING CURVE

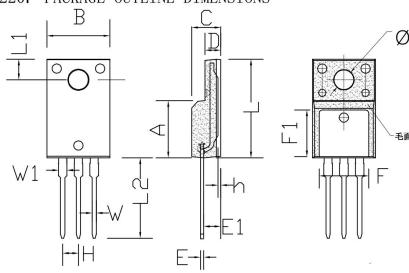


6 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
MBRD20200CT	TO-252	MBRD20200CT	Pb-free	Braid	3000/disc
MBR20200CT	TO-220	MBR20200CT	Pb-free	Tube	1000/box
MBRF20200CT	TO-220F	MBRF20200CT	Pb-free	Tube	1000/box
MBR20200CT	TO-263	MBR20200CT	Pb-free	Tube	1000/box

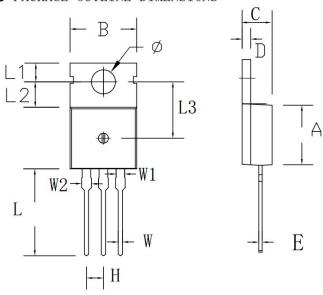
7 Dimensions





Curahal	DimensionsIn	Millimeters	Dimension:	sIn Inches
Symbol	min.	max.	min.	max.
А	8.80	9.30	0.346	0.366
В	10.00	10.50	0.394	0.413
С	4.30	4.90	0.169	0.193
D	2.30	2.70	0.091	0.106
L	15.55	16.15	0.612	0.636
h	0.40	0.60	0.016	0.024
L1	3.15	3.55	0.124	0.140
L2	12.65	13.35	0.498	0.526
W	0.70	0.90	0.028	0.035
W1	1.15	1.55	0.045	0.061
Н	2.54 TYP		0.100 TYP	
E	0.48	0.53	0.019	0.021
ф	2.90	3.40	0.114	0.134
E1	2.40	2.90	0.094	0.114
F	7.75	8.25	0.305	0.325
F1	7.35	7.85	0.289	0.309

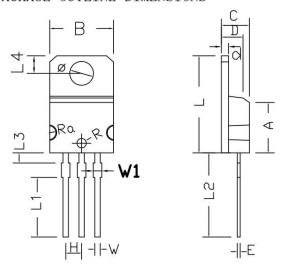
TO-220C PACKAGE OUTLINE DIMENSIONS



Cl 1	Dimensions In	Millimeters	Dimensions	In Inches
Symbol	min.	max.	min.	max.
A	8. 80	9. 30	0. 346	0.366
В	9. 70	10. 30	0.382	0.406
С	4. 25	4. 75	0. 167	0. 187
D	1. 20	1. 45	0.047	0.057
Е	0.40	0.60	0.016	0.024
Н	2. 54	TYP	0. 100	TYP
W	0.60	0. 95	0.024	0.037
W1	1.05	1. 45	0.041	0.057
W2	1. 20	1.60	0.047	0.063
L	12.60	13. 40	0. 496	0. 528
L1	2. 45	2. 95	0.096	0.116
L2	3. 45	3. 95	0. 136	0. 156
L3	8. 15	8. 65	0. 321	0.341
Φ	3, 50	3, 90	0. 138	0, 154



TO-220M PACKAGE OUTLINE DIMENSIONS



C 1 1	Dimensions I	n Millimeters	Dimensions	In Inches
Symbol	min.	max.	min.	max.
	MIN	MAX	MIN	MAX
A	7. 55	8.05	0. 297	0. 317
В	9.85	10. 25	0. 388	0.404
С	4. 20	4. 80	0. 165	0. 189
D	3. 20	3. 60	0. 126	0. 142
E	0.42	0. 47	0.017	0.019
L	15. 20	15. 60	0. 598	0.614
Н	2. 52	2. 56	0.099	0. 101
W	0.78	0.88	0.031	0.035
Φ	3.60	3.90	0.142	0. 154
R	0.72	0.78	0.028	0.031
Ra	9.00	10. 5	0.354	0.413
d	1. 10	1. 40	0.043	0. 055
L1	9.3	9.7	0.366	0.382
L2	13.00	13.60	0. 512	0. 535
L3	1. 20	1. 70	0.047	0.067
L4	2.60	3.0	0. 102	0.118
W1	1.10	1.50	0.043	0.059

9 Attentions

- Jiangsu Donghai Semiconductor Co.,Ltd. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
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- Product promotion is endless, our company will be dedicated to provide customers with better products.

10 Appendix

Revision history:

Date	REV.	Description	Page
2018.09.20	1.0	Original	
2022.1.20	1.1	Modify company name	ALL